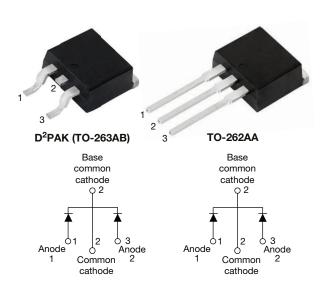


www.vishay.com

Vishay Semiconductors

Ultrafast Rectifier, 2 x 10 A FRED Pt®



VS-MURB2020CT-M3

VS-MURB2020CT-1-M3

PRIMARY CHARACTERISTICS							
I _{F(AV)}	2 x 10 A						
V_{R}	200 V						
V _F at I _F	0.85 V						
t _{rr}	35 ns						
T _J max.	175 °C						
Package	D ² PAK (TO-263AB), TO-262AA						
Circuit configuration	Common cathode						

FEATURES

- Ultrafast recovery time
- Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature



- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

DESCRIPTION / APPLICATIONS

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RA	ATINGS				
PARAMETER		SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage		V_{RRM}		200	V
Average rectified forward current	per leg	1		10	10 20 A
Average rectilled forward current	total device	I _{F(AV)}	Rated V _R , T _C = 145 °C	20	
Non-repetitive peak surge current pe	Non-repetitive peak surge current per leg			100	^
Peak repetitive forward current per l	epetitive forward current per leg I_{FM} Rated V_R , square wave, 20 kHz, $T_C = 145$ °C 20				
Operating junction and storage temp	oeratures	T _J , T _{Stg}		-65 to +175	°C

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	200	-	-			
		I _F = 8 A, T _J = 125 °C	ı	-	0.85	V		
Forward voltage	V_{F}	I _F = 16 A	-	-	1.15			
		I _F = 16 A, T _J = 125 °C	-	-	1.05			
Reverse leakage current	ı	$V_R = V_R$ rated	-	-	15			
neverse leakage current	I _R	$T_J = 150 ^{\circ}\text{C}, V_R = V_R \text{rated}$	-	-	250	μA		
Junction capacitance	C _T	V _R = 200 V	-	55	-	pF		
Series inductance	Ls	Measured lead to lead 5 mm from package body	-	8.0	-	nH		



www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST COM	NDITIONS	MIN.	TYP.	MAX.	UNITS	
Reverse recovery time		$I_F = 1.0 \text{ A}, dI_F/dt = 50$	A/μs, V _R = 30 V	-	-	35		
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	19	-	1	
		T _J = 25 °C	$I_F = 10 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 160 \text{ V}$	-	21	-	ns A	
		T _J = 125 °C		-	35	-		
Dook roopyony ourrent		T _J = 25 °C		-	1.9	-		
Peak recovery current	IRRM	T _J = 125 °C		-	4.8	-		
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	25	-		
		T _J = 125 °C		-	78	-	110	

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C		
Thermal resistance, junction-to-case per leg	R _{thJC}		-	-	2.5			
Thermal resistance, junction-to-ambient per leg	R _{thJA}		-	-	50	°C/W		
Thermal resistance, case-to-heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-			
Weight			-	2.0	-	g		
weight			-	0.07	-	OZ.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Mauline de de		Case style D ² PAK (TO-263AB)	yle D ² PAK (TO-263AB) MURB202		2020CT			
Marking device		Case style TO-262AA		MURB2	020CT-1			

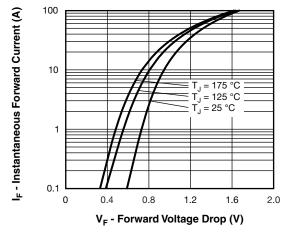


Fig. 1 - Typical Forward Voltage Drop Characteristics

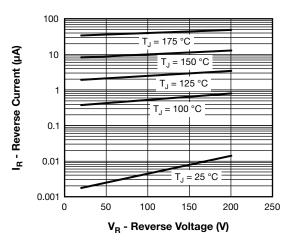


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

www.vishay.com

Vishay Semiconductors

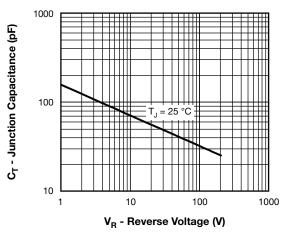


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

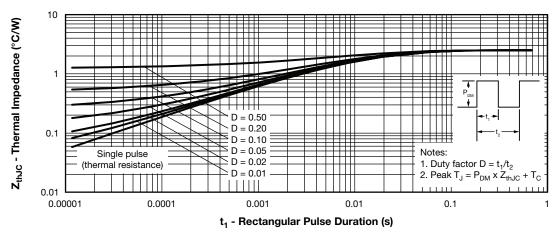


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

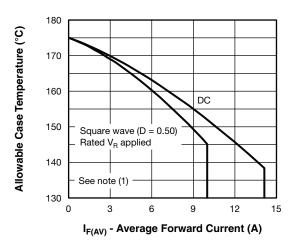


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

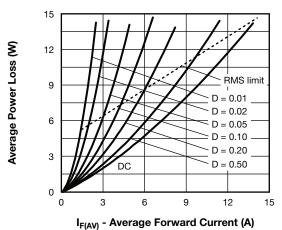


Fig. 6 - Forward Power Loss Characteristics

VS-MURB2020CT-M3, VS-MURB2020CT-1-M3

www.vishay.com

Vishay Semiconductors

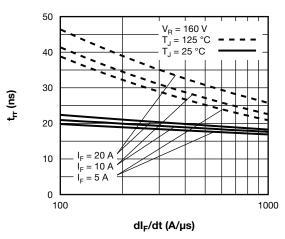


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

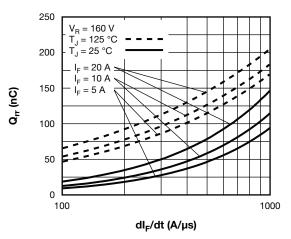
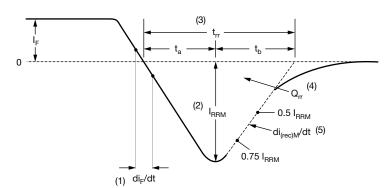


Fig. 8 - Typical Stored Charge vs. dl_F/dt

Note

 $\begin{array}{ll} \text{(1)} & \text{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \text{forward power loss} = I_{F(AV)} \times V_{FM} \text{ at } (I_{F(AV)}/D) \text{ (see fig. 6)}; \\ Pd_{REV} = \text{inverse power loss} = V_{R1} \times I_R \text{ (1 - D)}; I_R \text{ at } V_{R1} = \text{rated } V_R \\ \end{array}$



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} x I_{RRM}}{2}$$

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

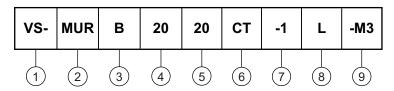
Fig. 9 - Reverse Recovery Waveform and Definitions

VS-MURB2020CT-M3, VS-MURB2020CT-1-M3

Vishay Semiconductors

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

Ultrafast MUR series

3 - B = D²PAK (TO-263AB) / TO-262AA

Current rating (20 = 20 A)

Voltage rating (20 = 200 V)

- CT = center tap (dual) TO-220 / D²PAK (TO-263AB) / TO-262AA

7 - • -1 = TO-262AA

• None = D^2PAK (TO-263AB)

8 - • None = tube (50 pieces)

• L = tape and reel (left oriented, for D²PAK (TO-263AB) package)

• R = tape and reel (right oriented, for D²PAK (TO-263AB) package)

9 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

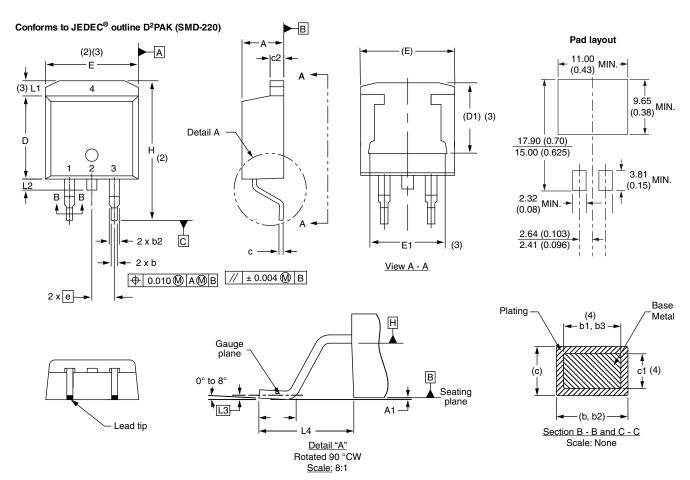
LINKS TO RELATED DOCUMENTS							
Dimensions —	D ² PAK (TO-263AB)	www.vishay.com/doc?96164					
Difficusions	TO-262AA	www.vishay.com/doc?96165					
Dark as adding information	D ² PAK (TO-263AB)	www.vishay.com/doc?95444					
Part marking information —	TO-262AA	www.vishay.com/doc?95443					
Packaging information	D ² PAK (TO-263AB)	www.vishay.com/doc?96424					
SPICE model		www.vishay.com/doc?95622					



Vishay Semiconductors

D²PAK

DIMENSIONS in millimeters and inches



SYMBOL	MILLIM	ETERS	INC	HES	NOTES 0.190 0.010	SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES	IOTES	STWIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
С	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC® outline TO-263AB

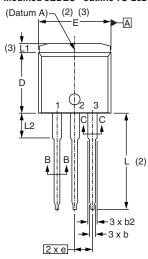
Revision: 13-Jul-17 **1** Document Number: 96164

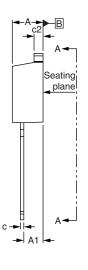
Vishay Semiconductors

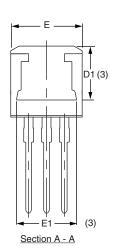
TO-262AA

DIMENSIONS in millimeters and inches

Modified JEDEC® outline TO-262







⊕ 0.010 **M** A**M** B

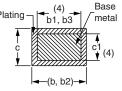
Lead assignments



Diodes 1. - Anode (two die)/open (one die)

2., 4. - Cathode

3. - Anode



Section B - B and C - C Scale: None

SYMBOL	MILLIN	IETERS	INC	NOTES			
OTHIDOL	MIN.	MAX.	MIN.	MAX.	NOTES		
Α	4.06	4.83	0.160	0.190			
A1	2.03	3.02	0.080	0.119			
b	0.51	0.99	0.020	0.039			
b1	0.51	0.89	0.020	0.035	4		
b2	1.14	1.78	0.045	0.070			
b3	1.14	1.73	0.045	0.068	4		
С	0.38	0.74	0.015	0.029			
c1	0.38	0.58	0.015	0.023	4		
c2	1.14	1.65	0.045	0.065			
D	8.51	9.65	0.335	0.380	2		
D1	6.86	8.00	0.270	0.315	3		
Е	9.65	10.67	0.380	0.420	2, 3		
E1	7.90	8.80	0.311	0.346	3		
е	2.54 BSC		0.100	BSC			
L	13.46	14.10	0.530	0.555			
L1	-	1.65	-	0.065	3		
L2	3.56	3.71	0.140	0.146			

Notes

(4) Dimension b1 and c1 apply to base metal only

Controlling dimension: inches

Revision: 30-Nov-17 Document Number: 96165

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

Thermal pad contour optional within dimension E, L1, D1 and E1

Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

单击下面可查看定价,库存,交付和生命周期等信息

>>Vishay(威世)